

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
60V	3.5mΩ@10V	130A

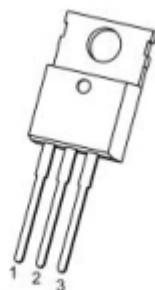
Feature

- Fast Switching
- Low Gate Charge and Rdson
- Low Reverse transfer capacitances
- 100% Single Pulse avalanche energy Test

Applications

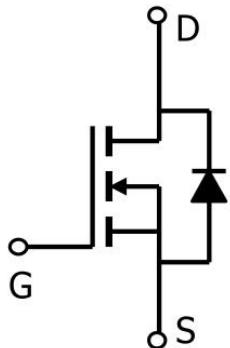
- Charger
- Battery management
- Power Switching application

Package

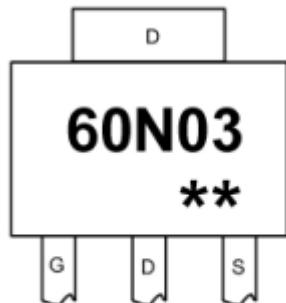


TO-220-3L-C(1:G 2:D 3:S)

Circuit diagram



Marking



60N03 : Product code
****** : Week code

Absolute maximum ratings

($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain source voltage	V_{DS}	60	V
Gate source voltage	V_{GS}	± 25	V
Continuous drain current($T_c=25^\circ\text{C}$)	I_D	130	A
Pulsed drain current	I_{DM}	520	A
Power dissipation($T_c=25^\circ\text{C}$)	P_D	210	W
Single pulsed avalanche energy ¹⁾	E_{AS}	784	mJ
Thermal resistance, junction-case	$R_{\theta JC}$	0.59	$^\circ\text{C}/\text{W}$
Operation and storage temperature	T_J, T_{STG}	-55~+150	$^\circ\text{C}$

Electrical characteristics

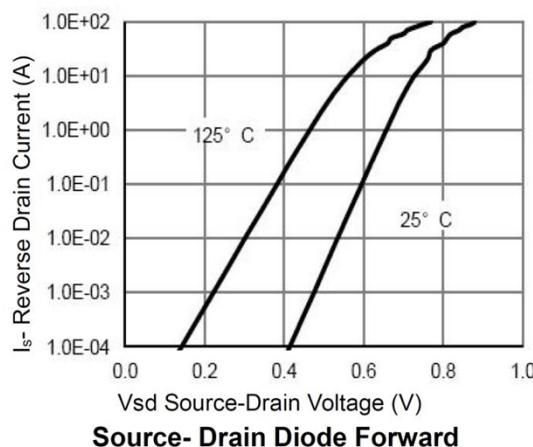
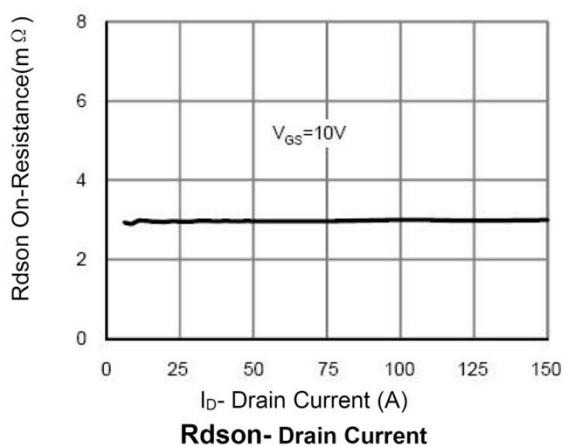
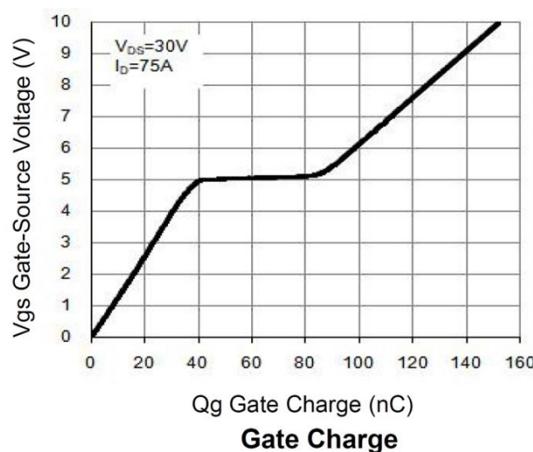
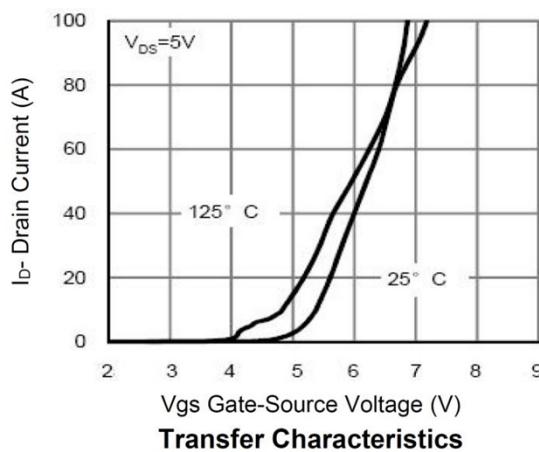
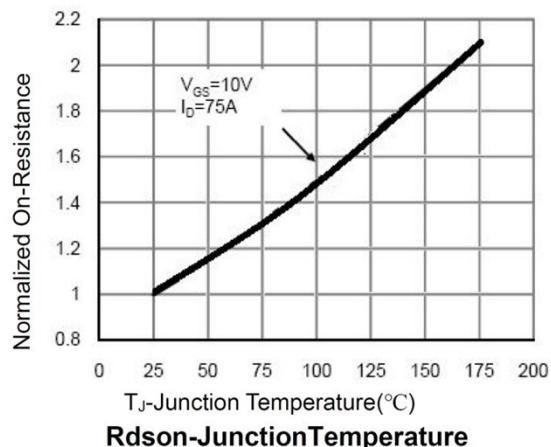
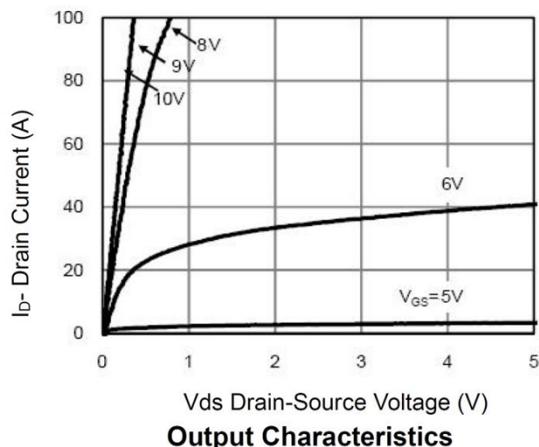
($T_A=25^\circ\text{C}$, unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	$\text{BV}_{(\text{BR})\text{DSS}}$	$V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$	60			V
Gate Threshold Voltage	$V_{GS(\text{th})}$	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	1.0		2.5	V
Drain Cut-Off Current	I_{DSS}	$V_{DS} = 48\text{V}, V_{GS} = 0\text{V}$			1	μA
Gate Leakage Current	I_{GSS}	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$			± 0.1	μA
Drain-Source ON Resistance	$R_{DS(\text{on})}$	$V_{GS} = 10\text{V}, I_D = 30\text{A}$		3.5	5	$\text{m}\Omega$
Dynamic Characteristics						
Input capacitance	C_{iss}	$V_{DS}=30\text{V}, V_{GS}=0\text{V}, f=1\text{MHz}$		5450		pF
Output capacitance	C_{oss}			610		
Transfer Capacitance	C_{rss}			480		
Switching Characteristics						
Total Gate Charge	Q_g	$V_{DS}=30\text{V}, V_{GS}=10\text{V}, I_D = 75\text{A}$		130		pF
Gate-Source Charge	Q_{gs}			22		
Gate-Drain Charge	Q_{gd}			56		
Turn-on delay time	$T_{d(on)}$	$V_{GS}=10\text{V}, V_{DS}=30\text{V}, R_G = 0.4\Omega, R_G = 2.5\Omega$		25		nS
Rise time	T_r			23		
Turn-off delay time	$T_{d(off)}$			91		
Fall time	T_f			36		
Drain-Source Body Diode Characteristics						
Source-Drain Diode Forward Voltage	V_{SD}	$V_{GS}=0\text{V}, I_S=1\text{A}$			1.2	V

Note :

1. E_{AS} is tested at starting $T_j = 25^\circ\text{C}$, $V_{DD} = 30\text{V}, V_{GS} = 10\text{V}, L = 0.5\text{mH}, R_g = 25\text{ m}\Omega$;

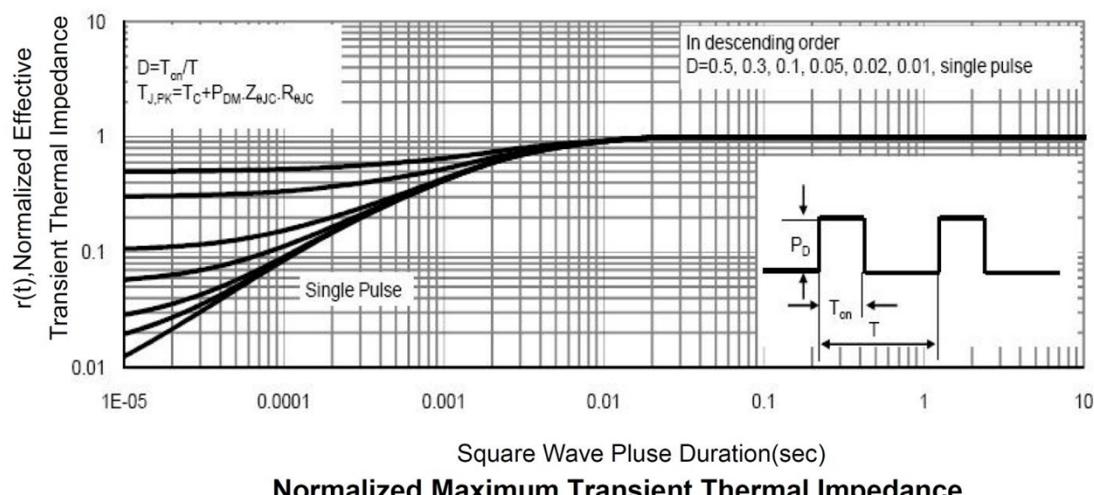
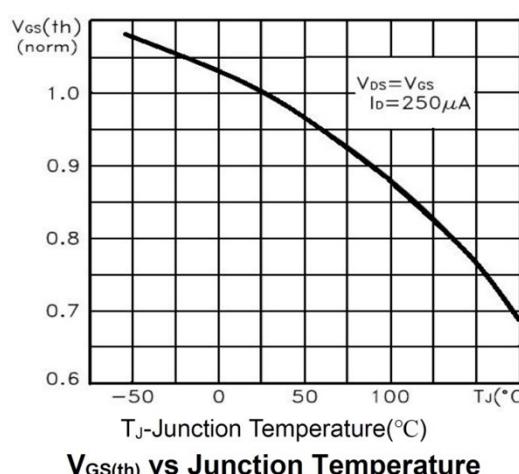
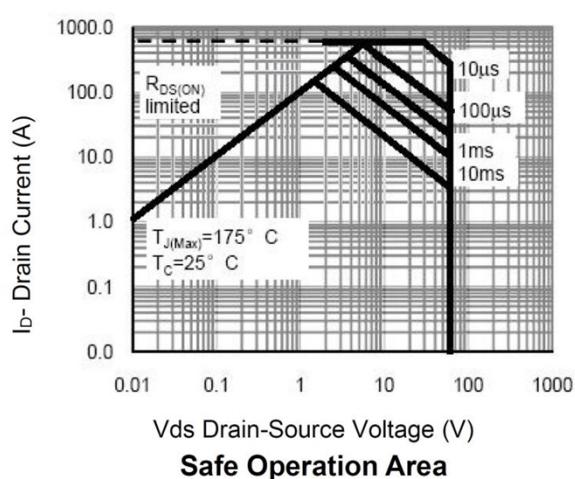
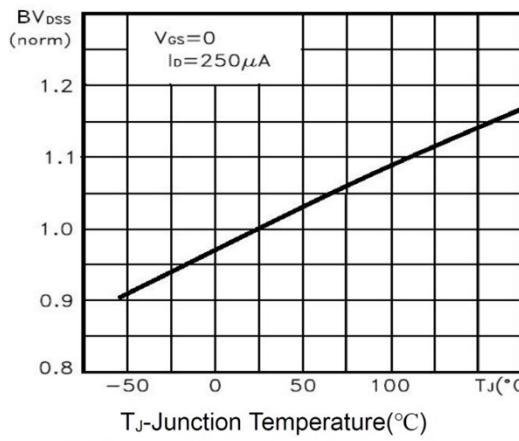
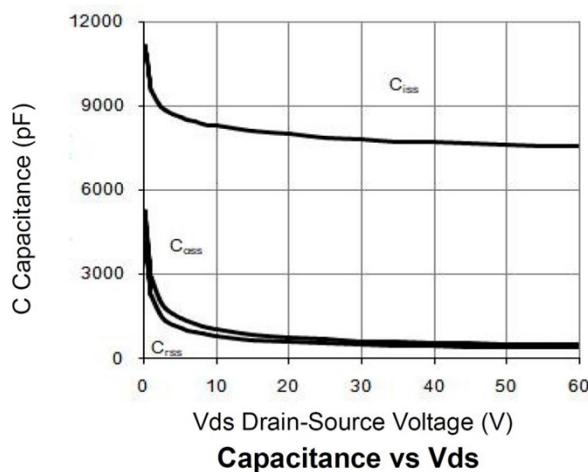
Typical Characteristics



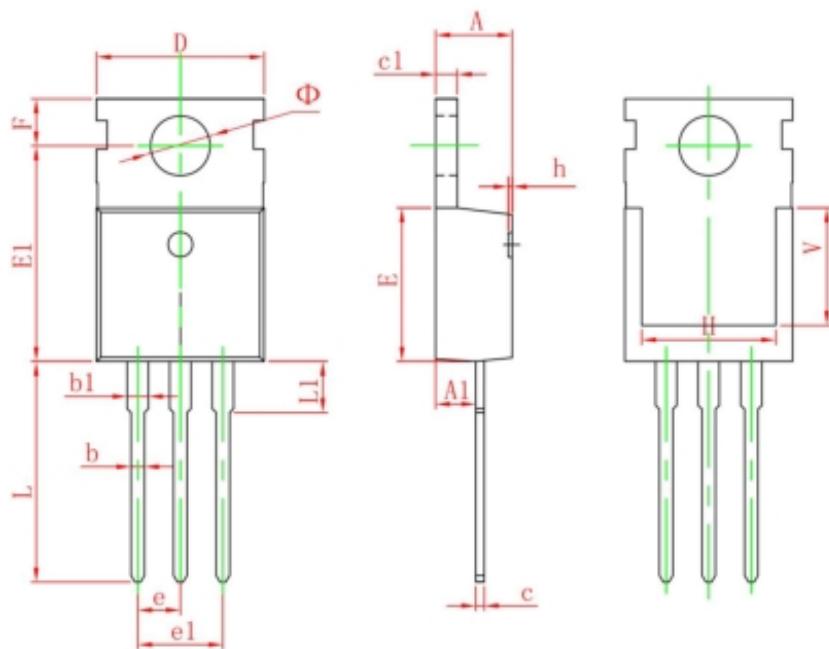


ZL MOSFET

ZL60N03A



TO-220-3L-C Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.400	4.600	0.173	0.181
A1	2.250	2.550	0.089	0.100
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.330	0.650	0.013	0.026
c1	1.200	1.400	0.047	0.055
D	9.910	10.250	0.390	0.404
E	8.950	9.750	0.352	0.384
E1	12.650	13.050	0.498	0.514
e	2.540 TYP.		0.100 TYP.	
e1	4.980	5.180	0.196	0.204
F	2.650	2.950	0.104	0.116
H	7.900	8.100	0.311	0.319
h	0.000	0.300	0.000	0.012
L	12.900	13.400	0.508	0.528
L1	2.850	3.250	0.112	0.128
v	6.900 REF.		0.276 REF.	
Φ	3.400	3.800	0.134	0.150